



# STGW30NC60WD

N-CHANNEL 30A - 600V - TO-247  
Ultra FAST Switching PowerMESH™ IGBT

## General features

Type	V <sub>CES</sub>	V <sub>CE(sat)</sub> Max @ 25°C	I <sub>C</sub> @ 100°C
STGW30NC60WD	600V	< 2.5V	30A

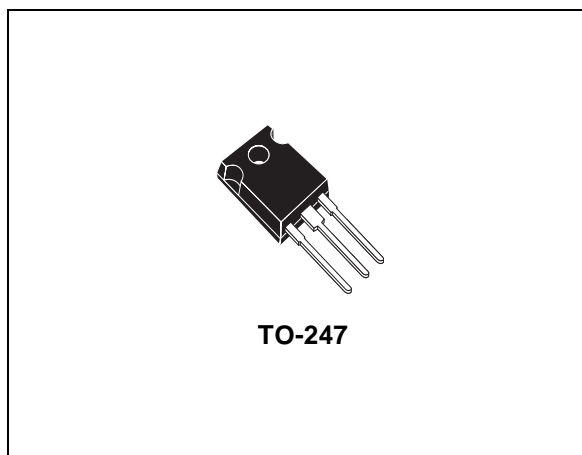
- High frequency operation
- Lower C<sub>RES</sub> / C<sub>IES</sub> ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery antiparallel diode

## Description

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix “W” identifies a family optimized for very high frequency application.

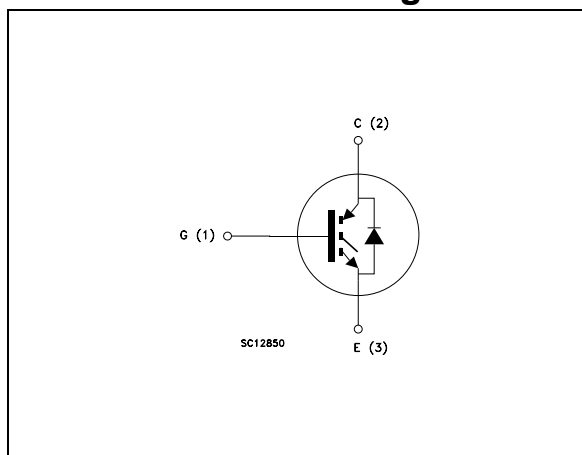
## Applications

- High frequency motor controls, inverters, ups
- HF, SMPS and PFC in both hard switch and resonant topologies



TO-247

## Internal schematic diagram



## Order codes

Sales Type	Marking	Package	Packaging
STGW30NC60WD	GW30NC60WD	TO-247	Tube

## Contents:

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuit</b> .....	<b>9</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Revision history</b> .....	<b>12</b>

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{GS} = 0$ )	600	V
$I_C$	Collector Current (continuous) at 25°C	60	A
$I_C$	Collector Current (continuous) at 100°C	30	A
$I_{CM}^{(1)}$	Collector Current (pulsed)	200	A
$V_{GE}$	Gate-Emitter Voltage	$\pm 20$	V
$P_{TOT}$	Total Dissipation at $T_C = 25^\circ\text{C}$	200	W
$T_{stg}$	Storage Temperature	- 55 to 150	°C
$T_j$	Operating Junction Temperature		
$T_L$	Maximum Lead Temperature for Soldering Purpose (1.6mm from case, for 10 sec.)	300	°C

1. Pulse width limited by max junction temperature

**Table 2. Thermal resistance**

		Min.	Typ.	Max.	Unit
Rthj-case	Thermal Resistance Junction-case			0.625	°C/W
Rthj-amb	Thermal Resistance Junction-ambient			62.5	°C/W

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}\text{C}$  unless otherwise specified)

**Table 3. Static**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collectro-Emitter Breakdown Voltage	$I_C = 1\text{mA}, V_{GE} = 0$	600			V
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15\text{V}, I_C= 20\text{A}, T_j= 25^{\circ}\text{C}$ $V_{GE}=15\text{V}, I_C= 20\text{A}, T_j= 125^{\circ}\text{C}$		2.1 1.8	2.5	V V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE}= V_{GE}, I_C= 250\mu\text{A}$	3.75		5.75	V
$I_{CES}$	Collector-Emitter Leakage Current ( $V_{CE} = 0$ )	$V_{CE} = \text{Max Rating}, T_c=25^{\circ}\text{C}$ $V_{CE} = \text{Max Rating}, T_c=125^{\circ}\text{C}$			10 1	$\mu\text{A}$ mA
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{CE} = 0$ )	$V_{GE} = \pm 20\text{V}, V_{CE} = 0$			$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{CE} = 15\text{V}, I_C= 20\text{A}$		15		S

**Table 4. Dynamic**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$C_{ies}$ $C_{oes}$ $C_{res}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25\text{V}, f = 1\text{MHz}, V_{GE}=0$		2080 175 52		pF pF pF
$Q_g$ $Q_{ge}$ $Q_{gc}$	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 390\text{V}, I_C = 20\text{A},$ $V_{GE} = 15\text{V},$ (see Figure 16)		102 17.5 47	140	nC nC nC
$I_{CL}$	Turn-Off SOA Minimum Current	$V_{clamp} = 480\text{V}, T_j = 150^{\circ}\text{C}$ $R_G = 10\Omega, V_{GE}= 15\text{V}$	200			A

**Table 5. Switching on/off (inductive load)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 390V, I_C = 20A$		29.5		ns
$t_r$	Current Rise Time	$R_G = 10\Omega, V_{GE} = 15V,$		12		ns
$(di/dt)_{on}$	Turn-on Current Slope	$T_J = 25^\circ C$ (see Figure 16)		1640		A/ $\mu s$
$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 390V, I_C = 20A$		29		ns
$t_r$	Current Rise Time	$R_G = 10\Omega, V_{GE} = 15V,$		13.5		ns
$(di/dt)_{on}$	Turn-on Current Slope	$T_J = 125^\circ C$ (see Figure 16)		1600		A/ $\mu s$
$t_r(V_{off})$	Off Voltage Rise Time	$V_{CC} = 390V, I_C = 20A,$		19.5		ns
$t_{d(off)}$	Turn-off Delay Time	$R_{GE} = 10\Omega,$		118		ns
$t_f$	Current Fall Time	$V_{GE} = 15V, T_J = 25^\circ C$ (see Figure 18)		27		ns
$t_r(V_{off})$	Off Voltage Rise Time	$V_{CC} = 390V, I_C = 20A,$		46		ns
$t_{d(off)}$	Turn-off Delay Time	$R_{GE} = 10\Omega, V_{GE} = 15V,$		151		ns
$t_f$	Current Fall Time	$T_J = 125^\circ C$ (see Figure 18)		38		ns

**Table 6. Switching energy (inductive load)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on Switching Losses	$V_{CC} = 390V, I_C = 20A$		116		$\mu J$
$E_{off}^{(2)}$	Turn-off Switching Losses	$R_G = 10\Omega, V_{GE} = 15V,$		181		$\mu J$
$E_{ts}$	Total Switching Losses	$T_J = 25^\circ C$ (see Figure 18)		297		$\mu J$
$E_{on}^{(1)}$	Turn-on Switching Losses	$V_{CC} = 390V, I_C = 20A$		239		$\mu J$
$E_{off}^{(2)}$	Turn-off Switching Losses	$R_G = 10\Omega, V_{GE} = 15V,$		355		$\mu J$
$E_{ts}$	Total Switching Losses	$T_J = 125^\circ C$ (see Figure 18)		594		$\mu J$

1.  $E_{on}$  is the turn-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pak diode, the co-pack diode is used as external diode. IGBTs & Diode are at the same temperature (25°C and 125°C)
2. Turn-off losses include also the tail of the collector current

Table 7. Collector-emitter diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_f$	Forward On-Voltage	$I_f = 10A$ $I_f = 10A, T_j = 125^\circ C$		1.5 1.1	2	V V
$t_{rr}$ $Q_{rr}$ $I_{rrm}$ S	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current Softness factor of the diode	$I_f = 20A, V_R = 50V,$ $di/dt=100A/\mu s, T_j=25^\circ C$ (see Figure 19)		44 66 3 0.375		ns nC A
$t_{rr}$ $Q_{rr}$ $I_{rrm}$ S	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current Softness factor of the diode	$I_f = 20A, V_R = 50V,$ $di/dt=100A/\mu s, T_j=125^\circ C$ (see Figure 19)		88 237 5.4 0.57		ns nC A

## 2.1 Electrical characteristics (curves)

Figure 1. Output characteristics

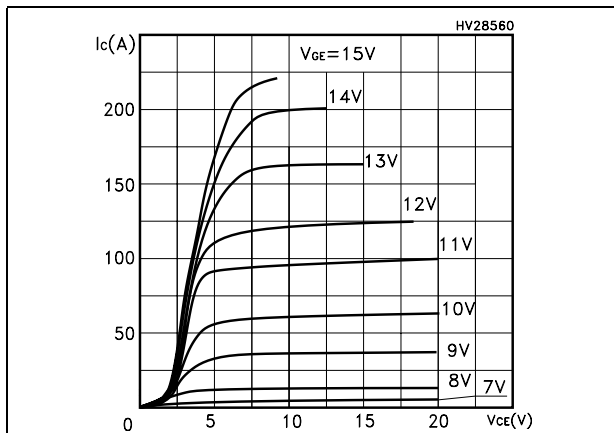


Figure 2. Transfer characteristics

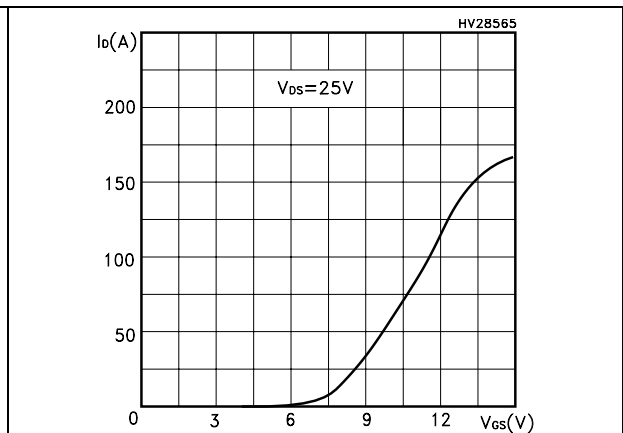


Figure 3. Transconductance

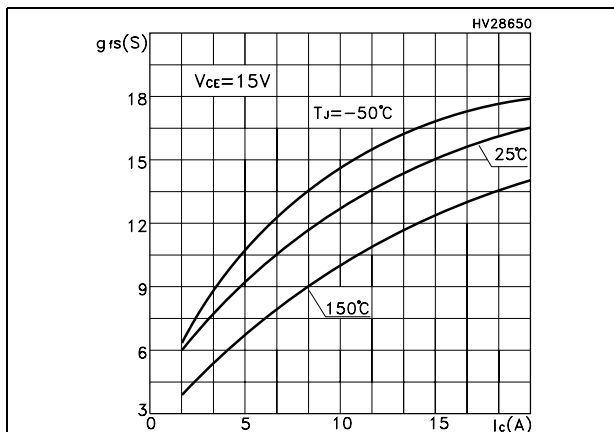


Figure 4. Collector-emitter on voltage vs temperature

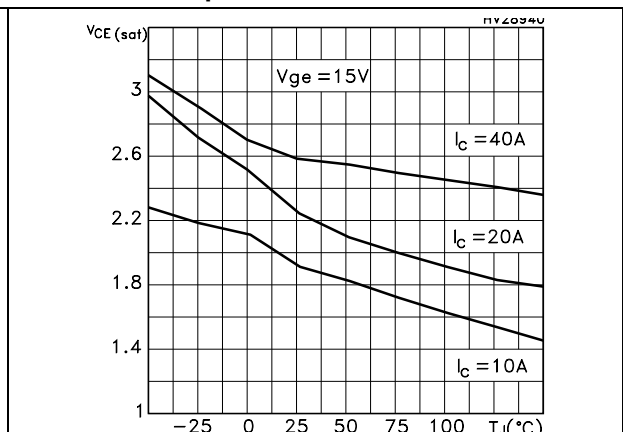


Figure 5. Gate charge vs gate-source voltage

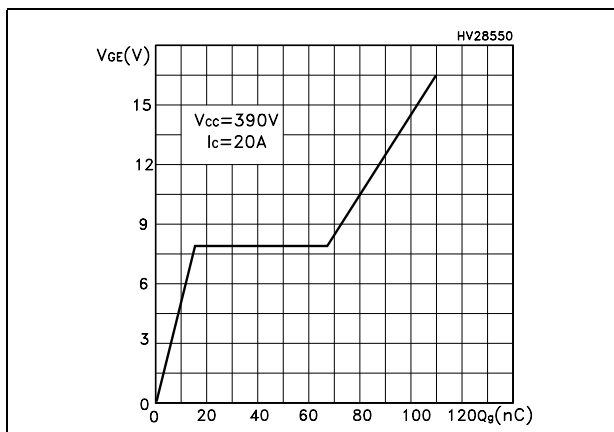


Figure 6. Capacitance variations

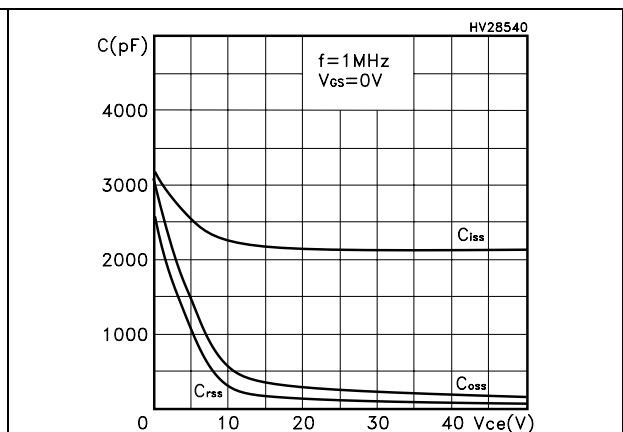


Figure 7. Normalized gate threshold voltage vs temperature

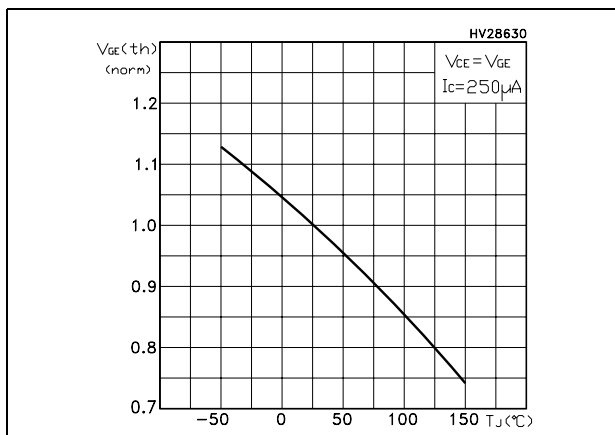


Figure 8. Collector-emitter on voltage vs collector current

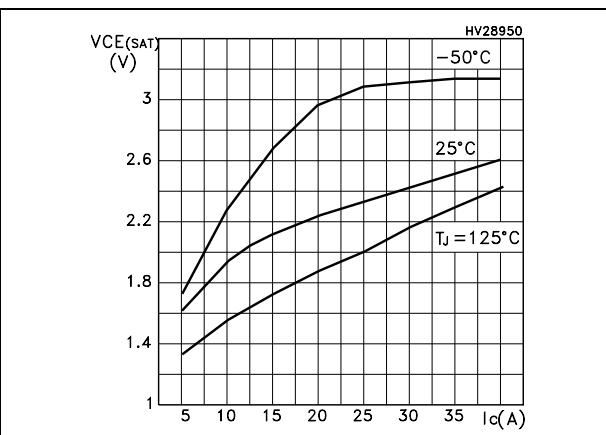


Figure 9. Normalized breakdown voltage vs temperature

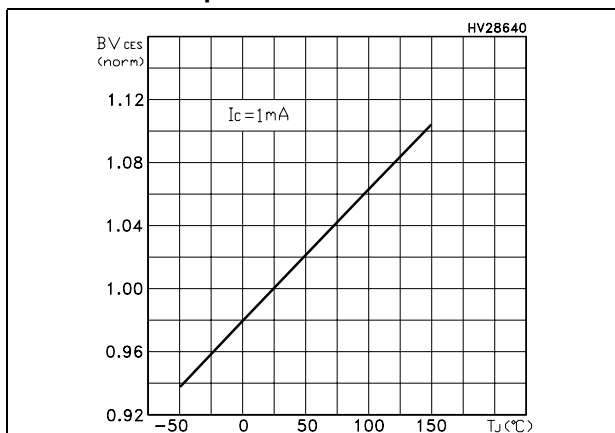


Figure 10. Switching losses vs temperature

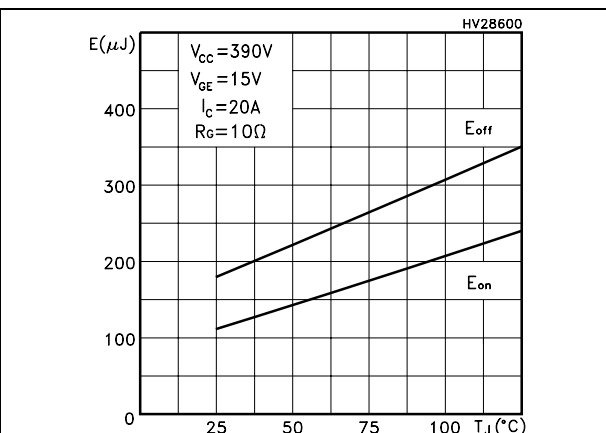


Figure 11. Switching losses vs gate resistance

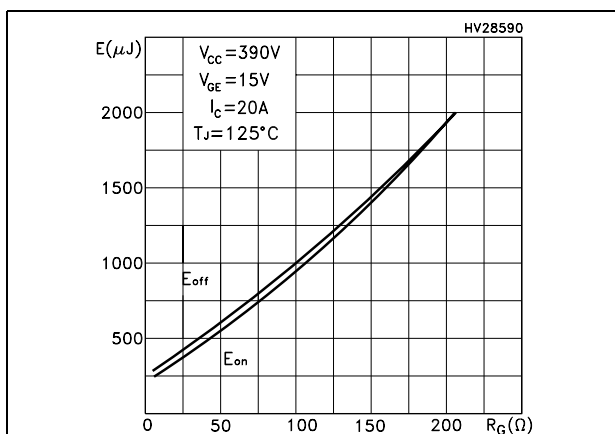


Figure 12. Switching losses vs collector current

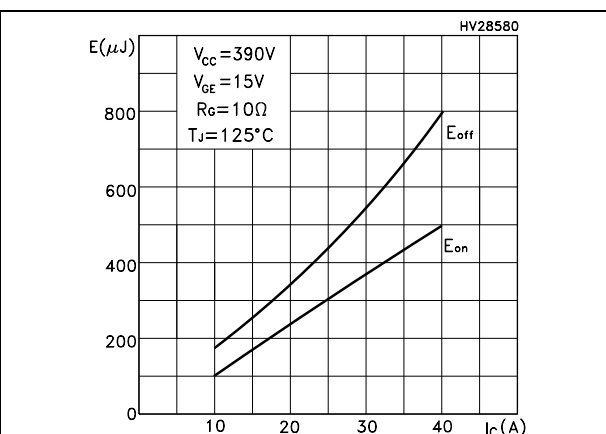




Figure 13. Thermal impedance

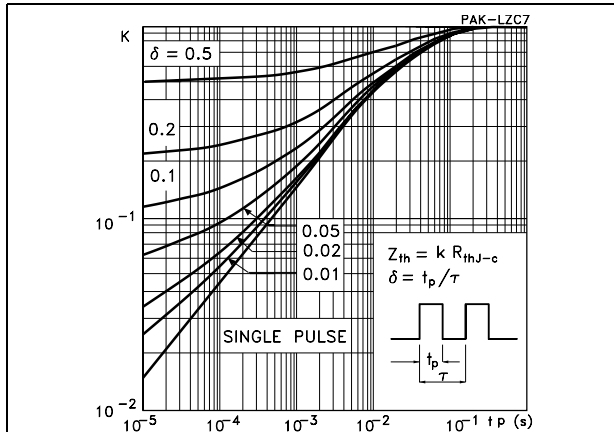


Figure 14. Turn-off SOA

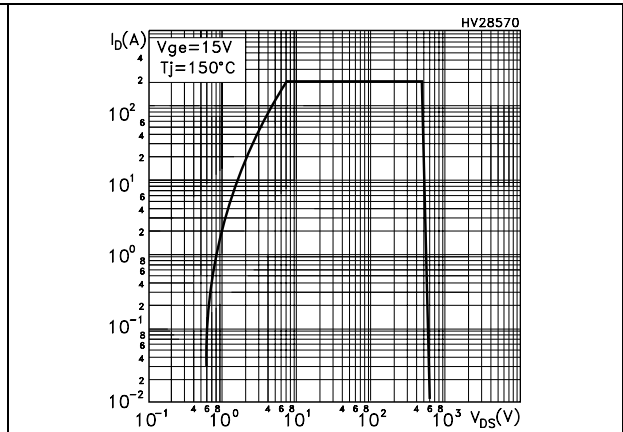
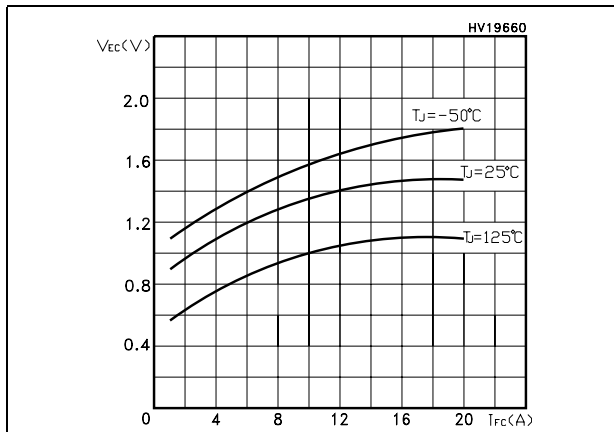


Figure 15. Emitter-collector diode characteristics



### 3 Test circuit

Figure 16. Test circuit for inductive load switching

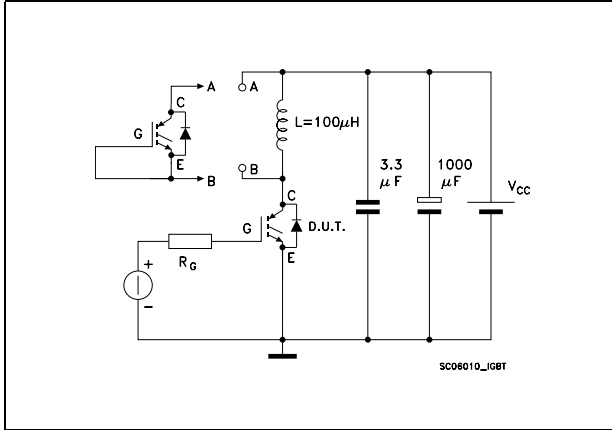


Figure 17. Gate charge test circuit

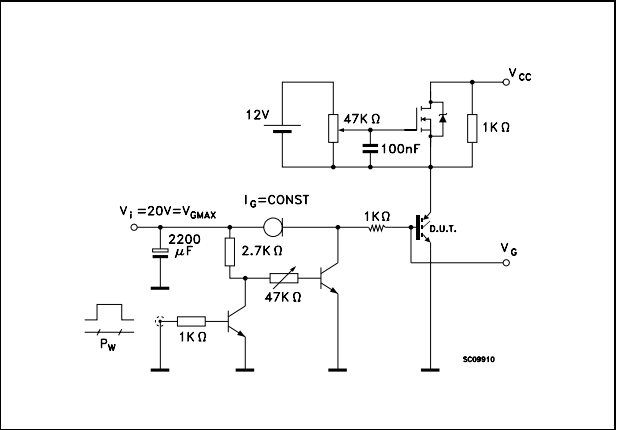


Figure 18. Switching waveform

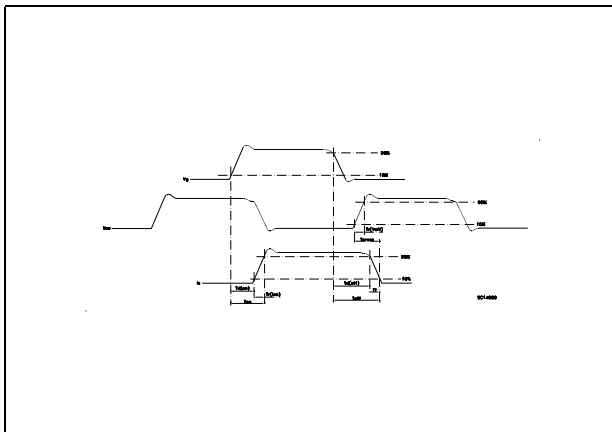
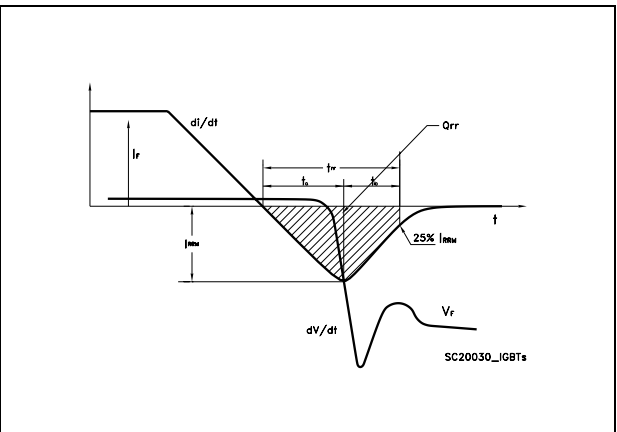


Figure 19. Diode recovery time waveform

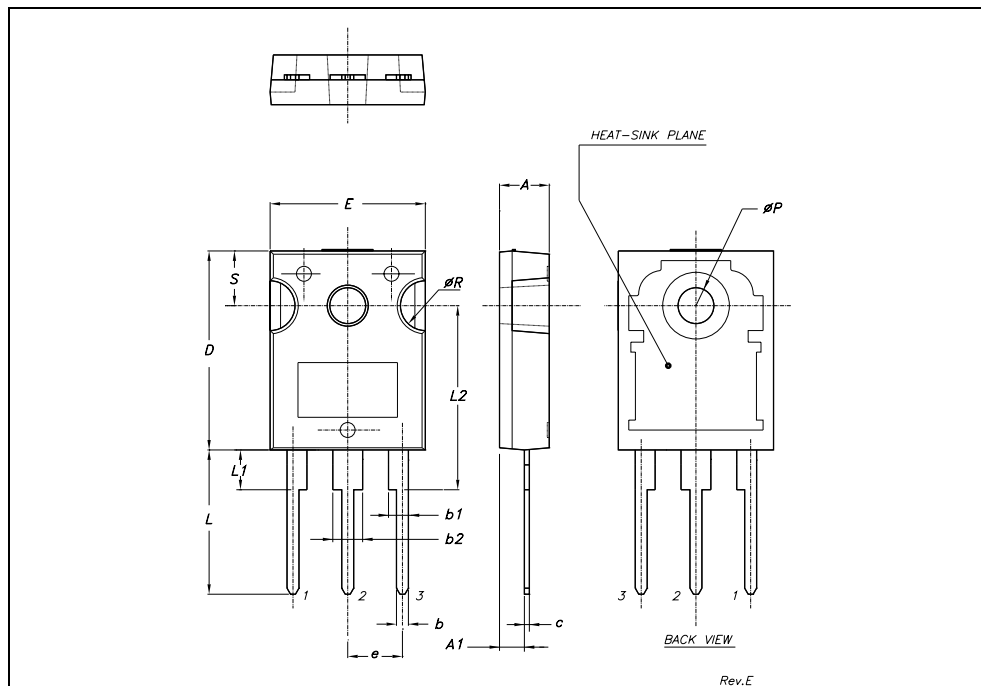


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

**TO-247 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



## 5 Revision history

**Table 8. Revision history**

Date	Revision	Changes
21-Nov-2005	1	Initial release.
29-Nov-2005	2	Modified <a href="#">Figure 4</a> and <a href="#">Figure 5</a>
06-Mar-2006	3	New template

**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT DESIGNED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)